

ABSTRACT

An emitter contact structure including a silicon substrate having a collector region, a base region within the collector region, and an emitter region within the base region. A base polysilicon layer positioned on the silicon substrate in contact with the base region and defining an aperture, with side walls, exposing the base and emitter regions of the silicon substrate. A spacer extending upwardly from the silicon substrate and formed to cover the side walls, the spacer covering the base region and partially covering the emitter region. An emitter polysilicon layer positioned entirely within the aperture in engagement with the emitter region, the spacer and the substrate without overlapping the base polysilicon layer.

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